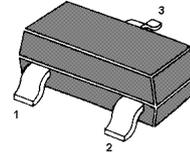
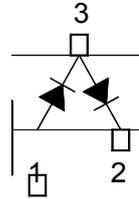


## SILICON EPITAXIAL PLANAR DIODE

for VHF~UHF band RF attenuator applications



Marking Code: **FP**  
SOT-23 Plastic Package

### Absolute Maximum Ratings ( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Reverse Voltage	$V_R$	50	V
Forward Current	$I_F$	50	mA
Junction Temperature	$T_j$	125	$^\circ\text{C}$
Storage Temperature Range	$T_s$	- 55 to + 125	$^\circ\text{C}$

### Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
Forward Voltage at $I_F = 10\text{ mA}$	$V_F$	-	-	1	V
Reverse Voltage at $I_R = 10\ \mu\text{A}$	$V_R$	50	-	-	V
Reverse Current at $V_R = 50\text{ V}$	$I_R$	-	-	0.1	$\mu\text{A}$
Total Capacitance at $V_R = 50\text{ V}$ , $f = 1\text{ MHz}$	$C_T$	-	0.25	-	pF
Series Resistance <sup>1)</sup> at $I_F = 10\text{ mA}$ , $f = 100\text{ MHz}$	$r_s$	-	7	-	$\Omega$

<sup>1)</sup>  $C_T$  is measured by 3 terminal method with capacitance bridge.

